NSN 5962-01-436-7052

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Altered item programmed using device 81349 m38510/20904bkx

Body Length:
0.640 inches
Body Width:
Between 0.300 inches and 0.420 inches
Body Height:
Between 0.045 inches and 0.090 inches
Maximum Power Dissipation Rating:
950.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
F016 c/d psp
Features Provided:
Bipolar and burn in, mil-std-883, class b and electrostatic sensitive and high impedance and monolithic and programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
14 input
Criticality Code Justification:
Cbbl
Case Outline Source And Designator:
F-6 mil-m-38510
Current Rating Per Characteristic:
185.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
Med read only memory boram
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source and -1.5 volts input and 5.5 volts input
Time Rating Per Chacteristic:
90.00 nanoseconds input to output access
Memory Device Type:
Prom
Special Features:
Altered item programmed using device 81240 m28E10/2000/hlv

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Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 beam lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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